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7	"High ) pp. 377			rostructure Field Effect Transis	tor," M. S. Sh	ur et al., Proce	edings of IS	DRS-97,
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OTHER DOCUMENTS (Including Author, Title, Date, Perlinent Pages, Etc.)  OTHER DOCUMENTS (Including Author, Title, Date, Perlinent Pages, Etc.)  "DC, Microwave, and High-Temperature Characteristics of Gan FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.  "Gan - AixGal-xN Beterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposium Proceedings Vol. 281 (1993), pp. 769-774.  EXAMINER  DATE CONSIDERED			·							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  "DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binarl et al., Inst. Phys. Conf. Set No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.  "GaN - AlxGa1-xN Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposiur Proceedings Vol. 281 (1993), pp.769-774.										
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  "DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Set No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.  "GaN - AlxGa1-xN Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposiur Proceedings Vol. 281 (1993), pp.769-774.						<del> </del>				
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  "DC, Microwave, and High-Temperature Characteristics of Gan FET Structures," S. C. Binari et al., Inst. Phys. Conf. Sei No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.  "Gan - AlxGal-xn Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposiur Proceedings Vol. 281 (1993), pp.769-774.  DATE CONSIDERED  DATE CONSIDERED			FOREIG	N PATENT DOCUMENTS						
"DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.  "GaN - AlxGa1-xN Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposiur Proceedings Vol. 281 (1993), pp.769-774.  DATE CONSIDERED  DATE CONSIDERED		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SS SUBCLASS	Commence of the commence of th			
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PET	or field-effect transistors," Applied								
HOA 0 2	MOCHEN	Gaska, R. et al., "Electron mobility in modulation-doped AlGaN-GaN heterostructures," Applied Physics Letters, Vol. 74, No. 2, 11 January 1999, pp. 287-289.  Khan, M.A. et al., "Current/voltage characteristic collapse in AlGaN/GaN heterostructure insulated gate field effect transistors at high drain bias," Electronics Letters, Vol. 30, No. 25, 8 December 1994, pp. 2175-2176.							
		Carrano, J.C. et al., "Very low dark current metal-semiconductor-metal ultraviolet photodetectors fabricated on single-crystal GaN epitaxial layers," Applied Physics Letters, Vol. 70, No. 15, 14 April 1997, pp. 1992-1994.							
		Chen, Q. et al., "Schottky barrier detectors on GaN for visible-blind ultraviolet detection," Applied Physics Letters, Vol. 70, No. 17, 28 April 1997, pp. 2277-2279.							
		Khan, M.A. et al., "AlGaN/GaN metal-oxide-semiconductor heterostructure field-effect transistors on SiC substrates," Applied Physics Letters, Vol. 77, No. 9, 28 August 2000, pp. 1339-1341.							
		Shur, M.S. and Khan, M.A., "GaN and AlGaN Dev Science Publishers, Series Optoelectronic Properties II, pp. 47-92, S. Pearton, Editor (1999).	rices: Field Effect Transistors and Phes of Semiconductors and Superlattice	otodetectors," Gordon and Breach es, Vol. 7 GaN and Related Materials					
		Shur, M.S. and Khan, M.A., "Wide Band Gap Semiconductors. Good Results and Great Expectations," Paper presented at 23rd Int. Symp. Compound Semiconductors, St. Petersburg, Russia, 23-27 September 1996, pp. 25-31.							
V		Khan, M.A. et al., "AlGaN/GaN Metal Oxide Semic Letters, Vol. 21, No. 2, February 2000, pp. 63-65.	conductor Heterostructure Field Effe	ect Transistor," IEEE Electron Device					
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7	5,424,227	06/1995	Dietric	h et al.					
Ì	5,990,531	11/1999	Taskar	et al.			/	7	
	6,298,079	10/2001	Tanaka	a et al.					
	6,316,793	11/2001	Sheppa	ard et al.					
	6,479,843	11/2002	Huang	et al.					
1	6,486,502	11/2002	Shepps	ard et al.					
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